

CONFIGURABLE MULTIPLE-FUNCTION GATE

Description

The 74LVC1G58 is a single 3-input positive configurable multiple function gate with a standard push-pull output. The output state is determined by eight patterns of 3-bit input. The user can chose the logic functions AND, OR, NAND, NOR, XOR, inverter or non-inverting buffer. All inputs can be connected to ground or V_{CC} as required. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down. The user is reminded that the device can simulate several types of logic gates, but may respond differently due to the Schmitt action at the inputs.

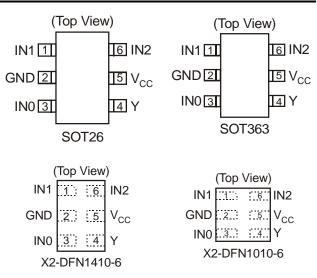
Features

- Wide Supply Voltage Range from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Exceeds JESD 22
 - 200-V Machine Model (A115-A)
 - 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- SOT26, SOT363, DF1410, and DFN1010: Available in "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)
 - Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
 - Halogen and Antimony Free. "Green" Device (Note 3)

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Assignments



Applications

- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide array of products such as:
 - PCs, networking, notebooks, netbooks, PDAs
 - Computer peripherals, hard drives, CD/DVD ROM
 - TV, DVD, DVR, set top box
 - Cell Phones, Personal Navigation / GPS
 - MP3 players ,Cameras, Video Recorders

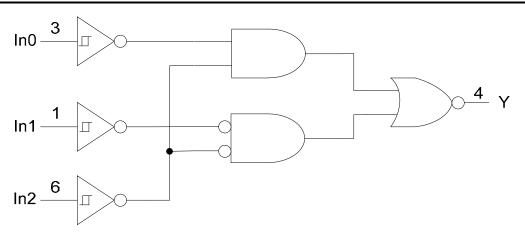


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Pin Descriptions

Pin Name	Function
IN1	Data Input
GND	Ground
IN0	Data Input
Y	Data Output
V _{CC}	Supply Voltage
IN2	Data Input

Logic Diagram



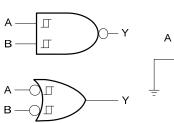
Function Table

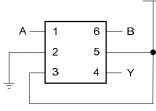
	Inputs		Output
IN2	IN1	IN0	Y
L	L	L	L
L	L	Н	Н
L	Н	L	L
L	Н	Н	Н
Н	L	L	Н
Н	L	Н	Н
Н	Н	L	L
Н	Н	Н	L



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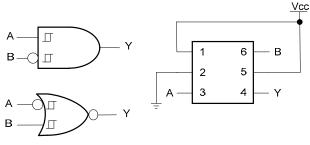
Logic Configurations



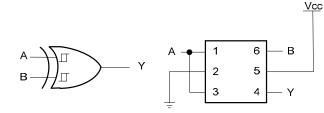


Vcc

Configuration 1 2-Input NAND Gate 2-Input OR Gate with Both Inputs Inverted



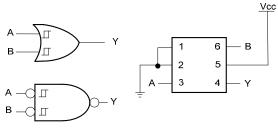
Configuration 3 2-Input AND Gate with B Input Inverted 2-Input NOR Gate with A Input Inverted



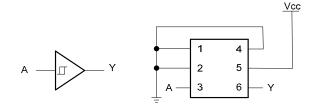
Configuration 5 2-Input XOR Gate

$ \begin{array}{c} A = \bigcirc \square \\ B = \square \\ \square \end{array} $	A — 1	6 — В
	– 2	5
	3	4 Y

Configuration 2 2-Input AND Gate with A Input Inverted 2-Input NOR Gate with B input Inverted



Configuration 4 2-Input OR Gate 2-Input NAND Gate with Both Inputs Inverted



Configuration 6 Buffer

Function Selection Table Logic Function Configuration 2-input NAND 1 2-input NAND with both inputs inverted 4 2-input AND with inverted input 2, 3 2-input NOR with inverted input 2, 3 2-input OR 4				
Logic Function	Configuration			
2-input NAND	1			
2-input NAND with both inputs inverted	4			
2-input AND with inverted input	2, 3			
2-input NOR with inverted input	2, 3			
2-input OR	4			
2-input OR with both inputs inverted	1			
2-input XOR	5			
1-input Buffer	6			



CONFIGURABLE MULTIPLE-FUNCTION GATE

Absolute Maximum Ratings (Note 4)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or IOFF state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
l _{IK}	Input Clamp Current VI < 0	-50	mA
I _{OK}	Output Clamp Current	-50	mA
Ι _Ο	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 5)

Symbol		Parameter	Min	Max	Unit
V _{CC}		Operating	1.65	5.5	V
		Data retention only	1.5		V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	Vcc	V
		$V_{CC} = 1.65 V$		-4	
І _{ОН} Н		$V_{CC} = 2.3V$		-8	
	High-level output current			-16	mA
		$V_{CC} = 3V$		-24	
		$V_{CC} = 4.5V$		-32	
		V _{CC} = 1.65V		4	
		$V_{CC} = 2.3V$		8	
I _{OL}	V1 Input Voltage V0 Output Voltage IOH High-level output current IOH Low-level output current IOL Low-level output current			16	mA
		$V_{CC} = 3V$		24	
		$V_{CC} = 4.5V$		32]
		$V_{CC} = 1.8V \pm 0.15V, 2.5V \pm 0.2V$		20	
Δt/ΔV	Input transition rise or fall rate	$V_{CC} = 3.3V \pm 0.3V$		10	ns/V
		$V_{CC} = 5V \pm 0.5V$		5]
T _A	Operating free-air temperature		-40	+125	°C

Notes: 5. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics $T_A = -40^{\circ}C$ to $+85^{\circ}C$ (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	V _{cc}	Min	Тур	Max	Unit
			1.65V	0.70		1.20	
\/-	Positive-going input threshold voltage		2.3V	1.11		1.60	
V_{T+}			3V	1.50		2.00	
			4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.72	
			2.3V	0.58		1.00	
V _T .	Negative-going input threshold voltage		3V	0.80		1.30	
	lineshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
ΔV _T Hysteresis (V _{T+} - V _{T-)}			2.3V	0.40		0.80	
			3V	0.35		1.00	
			4.5V	0.55		1.10	
			5.5V	0.60		1.20	
		Ι _{ΟΗ} = -100μΑ	1.65V to 5.5V	V _{CC} - 0.1			
		I _{OH} = -4mA	1.65V	1.2			
		I _{OH} = -8mA	2.3V	1.9			
V _{OH}	High Level Output Voltage	I _{OH} = -16mA	0)/	2.4			V
		I _{OH} = -24mA	3V	2.3			
		I _{OH} = -32mA	4.5V	3.8			
		I _{OL} = 100μA	1.65V to 5.5V			0.1	
		I _{OL} = 4mA	1.65V			0.45	
		I _{OL} = 8mA	2.3V			0.3	
V _{OL}	High-level Input Voltage	I _{OL} = 16mA	0)/			0.4	V
		I _{OL} = 24mA	3V			0.55	
		I _{OL} = 32mA	4.5			0.55	
II.	Input Current	$V_I = 5.5V$ or GND	0 to 5.5V			± 5	μA
I _{OFF}	Power Down Leakage Current	$V_{\rm I}$ or $V_{\rm O}$ = 5.5V	0			± 10	μA
I _{CC}	Supply Current	$V_I = 5.5V$ of GND $I_O=0$	1.65V to 5.5V			10	μA
ΔI _{CC}	Additional Supply Current	One input at V_{CC} -0.6V Other inputs at V_{CC} or GND	3V to 5.5V			500	μA



Electrical Characteristics $T_A = -40^{\circ}C$ to $+125^{\circ}C$ (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
V _{T+}	Positive-going input		3V	1.50		2.00	
	threshold voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.75	
			2.3V	0.58		1.03	
V _T -	Negative-going input		3V	0.80		1.33	
	threshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
			2.3V	0.37		0.80	
ΔV_T	Hysteresis (V _{T+} - V _{T-)}		3V	0.32		1.00	
			4.5V	0.50		1.20	
			5.5V	0.55		1.40	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} -0.1			
		I _{OH} = -4mA	1.65V	0.95			
		I _{OH} = -8mA	2.3V	1.7			.,
V _{OH}	High Level Output Voltage	I _{OH} = -16mA	3V	1.9			V
		I _{OH} = -24mA		2.0			
		I _{OH} = -32mA	4.5V	3.4			
		I _{OL} = 100μA	1.65V to 5.5V			0.1	
		I _{OL} = 4mA	1.65V			0.7	
		I _{OL} = 8mA	2.3V			0.45	
V _{OL}	High-level Input Voltage	I _{OL} = 16mA	01/			0.6	V
		I _{OL} = 24mA	3V			0.8	
		$I_{OL} = 32mA$	4.5			0.8	
lı	Input Current	$V_{I} = 5.5V \text{ or GND}$	0 to 5.5V			± 100	μA
I _{OFF}	Power Down Leakage Current	$V_{\rm I}$ or $V_{\rm O}$ = 5.5V	0			± 200	μA
lcc	Supply Current	V _I = 5.5V of GND I _O =0	1.65V to 5.5V			200	μA
ΔI _{CC}	Additional Supply Current	One input at V_{CC} -0.6V Other inputs at V_{CC} or GND	3V to 5.5V			5000	μΑ



Electrical Characteristics (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
CI	Input Capacitance	$V_I = V_{CC} - or GND$	3.3		3.5		pF
		SOT26			204		
	Thermal Resistance Junction- to-Ambient	SOT363			371		°C/W
θ_{JA}		X2-DFN1410-6	(Note 6)		430		
		X2-DFN1010-6			510		
		SOT26			52		
	Thermal Resistance Junction-	SOT363			143		0.0.0.1
θ _{JC}	to-Case	X2-DFN1410-6	(Note 6)		190		°C/W
		X2-DFN1010-6			250		

Notes: 6. Test condition for SOT26, SOT363, X2-DFN1410-6 and X2-DFN1010-6: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Switching Characteristics

Parameter	From	ТО	± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
	(Input)	(Input) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Y	1.0	14.4	0.7	8.3	0.7	6.3	0.7	5.1	ns

$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$, CL = 30 or 50pF as noted (see Figure 1)

Parameter	From	то	V _{CC} = 1.8V ± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
	(Input)	(Input) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Y	1.0	18.0	0.7	10.4	0.7	7.9	0.7	6.4	ns

Operating Characteristics

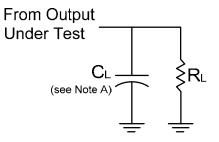
$T_A = +25^{\circ}C$

	Parameter	Test Conditions	V _{CC} = 1.8V Typ.	V _{CC} = 2.5V Typ.	V _{CC} = 3.3V Typ.	V _{CC} = 5V Typ.	Unit
C _{pd}	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF

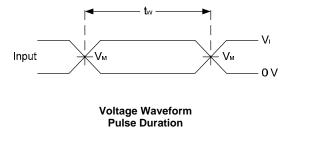


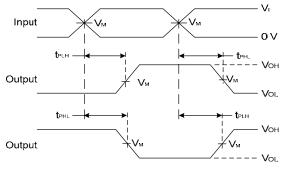
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Parameter Measurement Information



Vcc	Inputs		VM	CL	RL	
	VI	t _r /t _f				
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	30pF	1ΚΩ	
2.5V±0.2V	Vcc	≤2ns	V _{CC} /2	30pF	500Ω	
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω	
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	50pF	500Ω	





Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1. Load Circuit and Voltage Waveforms

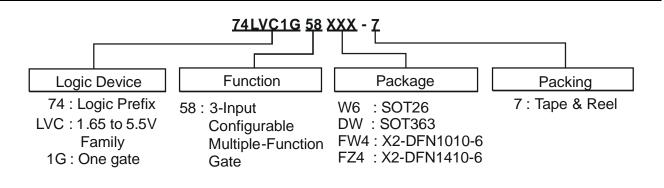
Notes:

- A. Includes test lead and test apparatus capacitance.
- B. All pulses are supplied at pulse repetition rate \leq 10 MHz
- C. Inputs are measured separately one transition per measurement
- D. t_{PLH} and t_{PHL} are the same as t_{PD}



CONFIGURABLE MULTIPLE-FUNCTION GATE

Ordering Information



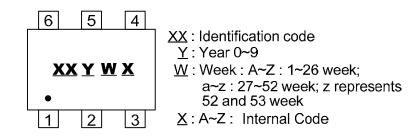
	Davias	Packaging		7" Tape and Reel		
	Device	Package Code	(Note 7)	Quantity	Part Number Suffix	
Pb,	74LVC1G58W6-7	W6	SOT26	3000/Tape & Reel	-7	
Pb	74LVC1G58DW-7	DW	SOT363	3000/Tape & Reel	-7	
Pb	74LVC1G58FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7	
Pb,	74LVC1G58FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7	

Notes: 7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



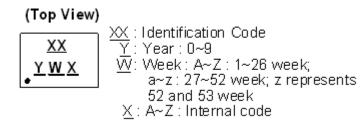
Marking Information

(1) SOT26, SOT363



Part Number	Package	Identification Code
74LVC1G58W6	SOT26	ТΧ
74LVC1G58DW	SOT363	ТХ

(2) X2-DFN1010-6, X2-DFN1410-6



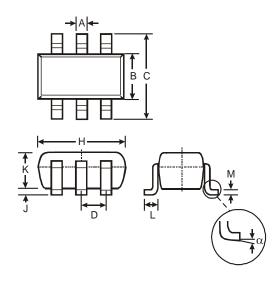
Part Number	Package	Identification Code
74LVC1G58FW4	X2-DFN1010-6	ТΧ
74LVC1G58FZ4	X2-DFN1410-6	ТΧ



CONFIGURABLE MULTIPLE-FUNCTION GATE

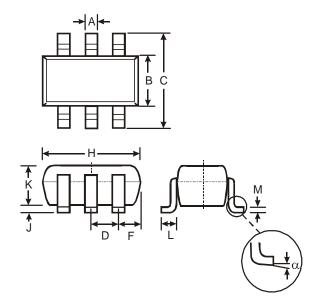
Package Outline Dimensions (All Dimensions in mm)

(1) SOT26



SOT26				
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
В	1.50	1.70	1.60	
с	2.70	3.00	2.80	
D			0.95	
Н	2.90	3.10	3.00	
J	0.013	0.10	0.05	
к	1.00	1.30	1.10	
1	0.35	0.55	0.40	
Μ	0.10	0.20	0.15	
α	0°	8°		
All D	imensi	ons in	mm	

(2) SOT363



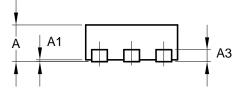
	SOT363		
Dim	Min	Max	
Α	0.10	0.30	
В	1.15	1.35	
C	2.00	2.20	
D	D 0.65 Typ		
F	0.40	0.45	
н	1.80	2.20	
J	0	0.10	
к	0.90	1.00	
_	0.25	0.40	
М	0.10	0.22	
α	0°	8°	
All Di	mensions	in mm	

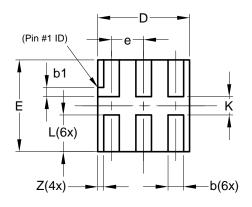


CONFIGURABLE MULTIPLE-FUNCTION GATE

Package Outline Dimensions (All Dimensions in mm)

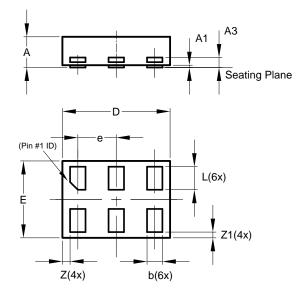
(3) X2-DFN1010-6





X2-DFN1010-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3			0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е	_		0.35	
L	0.35	0.45	0.40	
Κ	0.15	_		
Z	_		0.065	
All	Dimens	sions in	mm	

(4) X2-DFN1410-6



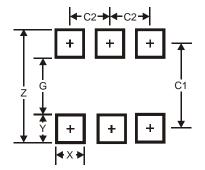
X2-DFN1410-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3			0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
E	0.95	1.05	1.00	
е		_	0.50	
L	0.25	0.35	0.30	
Z			0.10	
Z1	0.045	0.105	0.075	
All I	Dimensi	ions in I	nm	



CONFIGURABLE MULTIPLE-FUNCTION GATE

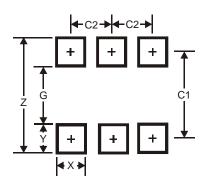
Suggest Pad Layout

(1) SOT26



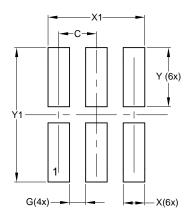
Dimensions	Value (in mm)
Z	3.20
G	1.60
х	0.55
Y	0.80
C1	2.40
C2	0.95

(2) SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

(3) X2-DFN1010-6



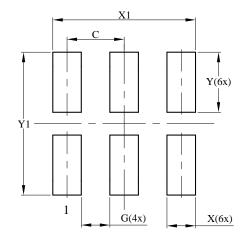
Dimensions	Value (in mm)
С	0.350
G	0.150
Х	0.200
X1	0.900
Y	0.550
Y1	1.250



CONFIGURABLE MULTIPLE-FUNCTION GATE

Suggest Pad Layout

(4) X2-DFN1410-6



Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Y	0.525
Y1	1.250



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LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products or systems.

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